

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.: Not yet assigned
Applicants: Christian DUSSARRAT, et al.
Filed Internationally: April 8, 2004
US National: Herewith
Title: METHODS FOR PRODUCING SILICON NITRIDE FILMS BY VAPOR-PHASE GROWTH
TC/A.U: Unknown
Examiner: Unknown
Docket No.: Serie 6070
Customer No.: 000040582

PRELIMINARY AMENDMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Prior to an examination of the merits of the above-identified U.S. patent application under 37 C.F.R. § 1.115, please first amend the application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Claims begin on page 4 of this paper.

Amendments to the Abstract begin on page 8 of this paper.

Remarks begin on page 9 of this paper.

An Appendix including the Abstract is attached following page 9 of this paper.